

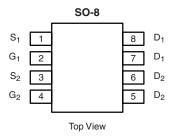
SI9926CDY-T1-GE3-VB Datasheet Dual N-Channel 20-V (D-S) MOSFET

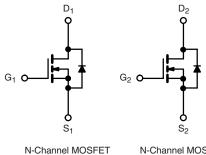
PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)		
20	0.019 at V _{GS} = 4.5 V	7.1		
	0.026 at V _{GS} = 2.5 V	6.0		

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET ٠
- 100 % R_g Tested
 Compliant to RoHS Directive 2002/95/EC







N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25 \text{ °C}$, unless otherwise noted					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	20		
Gate-Source Voltage		V _{GS}	± 12	V	
	T _A = 25 °C	- I _D	7.1		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		5.7	۸	
Pulsed Drain Current (10 µs Pulse Width)		I _{DM}	40	A	
Continuous Source Current (Diode Conduction) ^a		۱ _S	1.7		
Marian David Disabati and	T _A = 25 °C	PD	2	w	
Maximum Power Dissipation ^a	T _A = 70 °C	D'D	1.3	vv	
Operating Junction and Storage Temperature Range	Э	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Maximum Junction-to-Ambient ^a	R _{thJA}	62.5	°C/W		

Notes:

a. Surface Mounted on FR4 board, t \leq 10 s.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	0.6		1.5	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			± 100	nA	
Zara Cata Valtaga Drain Current	I _{DSS}	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	μA	
Zero Gate Voltage Drain Current		$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}$	20			А	
	P	V _{GS} = 4.5 V, I _D = 7.1 A		0.019		Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 6.0 \text{ A}$		0.026			
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 7.1 A		27		S	
Diode Forward Voltage ^a	V _{SD}	$I_{\rm S} = 1.7$ A, $V_{\rm GS} = 0$ V			1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			9.5			
Gate-Source Charge	Q _{gs}	V_{DS} = 10 V, V_{GS} = 4.5 V, I_{D} = 7.1 A		1.5		nC	
Gate-Drain Charge	Q _{gd}			2.5			
Gate Resistance	Rg	f = 1 MHz		1.6	2.7	Ω	
Turn-On Delay Time	t _{d(on)}			10			
Rise Time	t _r	V_{DD} = 10 V, R_L = 10 Ω		15			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ 1 A, V_{GEN} = 4.5 V, R_g = 10 Ω		38		ns	
Fall Time	t _f			25			
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.7 A, dl/dt = 100 A/μs		26			

Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

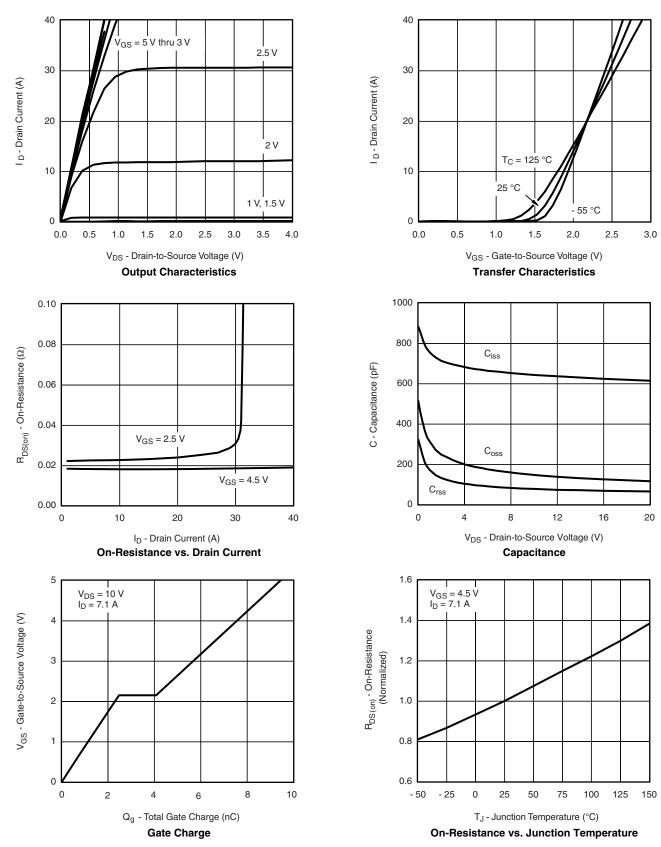
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



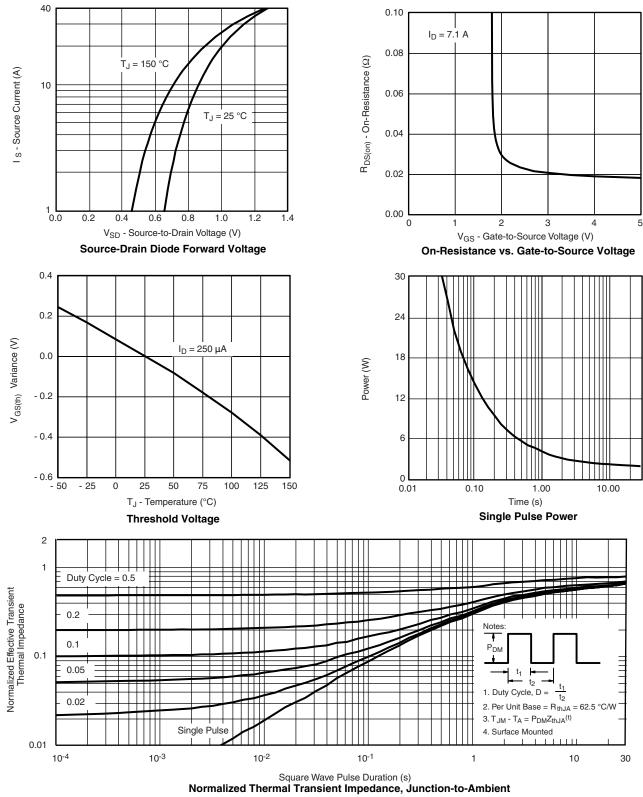


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





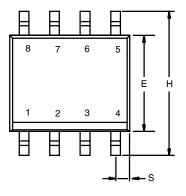
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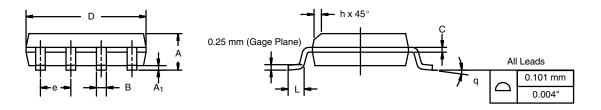




SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



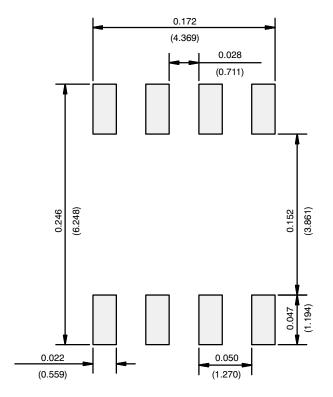


	MILLIM	IETERS	INC	HES	
DIM	Min	Мах	Min	Max	
A	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498					

SI9926CDY-T1-GE3-VB



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)



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